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etching the conductive material layer outside the organic patterns to expose the first photoresist pattern and form the connection patterns covered by the respective organic patterns; and

removing the first photoresist pattern and the organic 5 patterns.

8. The method according to claim 6, further comprising forming a common electrode on the second passivation layer and including bar-shaped openings in the pixel region when forming the gate auxiliary pad electrode and the data aux- 10 iliary pad electrode.

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